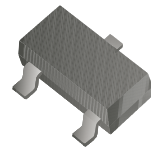


CMS2302-HF

N-Channel
RoHS Device
Halogen Free



V(BR)DSS	RDS(on)MAX	ID
20V	55mΩ @ 4.5V	3.6A
	75mΩ @ 2.5V	

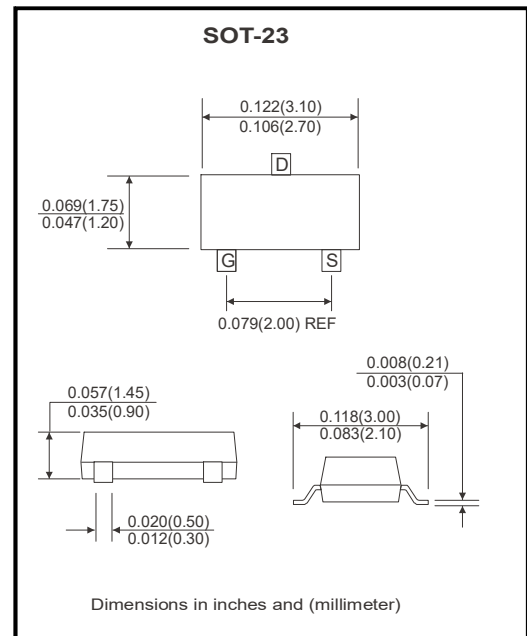
Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

Description

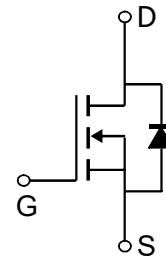
The CMS2302 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the small power switching and load switch applications.

The CMS2302 meet the RoHS and Green Product requirement with full function reliability approved.



Circuit diagram

- G : Gate
- S : Source
- D : Drain



Maximum Ratings (at Ta=25 °C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current ¹ , $V_{GS}@4.5V$	$I_D @TA=25^{\circ}C$	3.6	A
Continuous Drain Current ¹ , $V_{GS}@4.5V$	$I_D @TA=70^{\circ}C$	2.8	A
Pulsed Drain Current ²	I_{DM}	14.4	A
Power Dissipation ³	$P_D @TA=25^{\circ}C$	1.0	W
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	°C

Thermal Data

Parameter	Symbol	Max. Ratings	Unit
Thermal Resistance Junction-ambient ¹	$R_{\theta JA}$	125	°C/W

Electrical Characteristics (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV_{DSS}	20	-	-	V	$V_{GS}=0, I_D=250\mu\text{A}$
Gate Threshold Voltage	$V_{GS(th)}$	0.4	-	1.2	V	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$
Forward Transconductance	g_{fs}	-	10	-	S	$V_{DS}=5\text{V}, I_D=3\text{A}$
Gate-Source Leakage Current	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 12\text{V}$
Drain-Source Leakage Current($T_J=25^{\circ}\text{C}$)	I_{DSS}	-	-	1	μA	$V_{DS}=16\text{V}, V_{GS}=0$
Drain-Source Leakage Current($T_J=55^{\circ}\text{C}$)		-	-	5	μA	$V_{DS}=16\text{V}, V_{GS}=0$
Static Drain-Source On-Resistance ²	$R_{DS(on)}$	-	-	55	$\text{m}\Omega$	$V_{GS}=4.5\text{V}, I_D=3\text{A}$
		-	-	75		$V_{GS}=2.5\text{V}, I_D=2\text{A}$
Total Gate Charge ²	Q_g	-	4.6	-	nC	$I_D=3\text{A}$ $V_{DS}=15\text{V}$ $V_{GS}=4.5\text{V}$
Gate-Source Charge	Q_{gs}	-	0.7	-		
Gate-Drain ("Miller") Charge	Q_{gd}	-	1.5	-		
Turn-on Delay Time ²	$T_{d(on)}$	-	1.6	-	ns	$V_{DS}=10\text{V}$ $I_D=3\text{A}$ $V_{GS}=4.5\text{V}$ $R_G=3.3\Omega$
Rise Time	T_r	-	42	-		
Turn-off Delay Time	$T_{d(off)}$	-	14	-		
Fall Time	T_f	-	7	-		
Input Capacitance	C_{iss}	-	310	-	pF	$V_{GS}=0\text{V}$ $V_{DS}=15\text{V}$ $f=1.0\text{MHz}$
Output Capacitance	C_{oss}	-	49	-		
Reverse Transfer Capacitance	C_{rss}	-	35	-		

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Diode Forward Voltage ²	V_{SD}	-	-	1.2	V	$I_S=1\text{A}, V_{GS}=0\text{V}, T_J=25^{\circ}\text{C}$
Continuous Source Current ^{1,4}	I_S	-	-	3.6	A	$V_G=V_D=0\text{V}$, Force Current

Notes: 1. Surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2. The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

3. The power dissipation is limited by 150 $^{\circ}\text{C}$ junction temperature.

4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

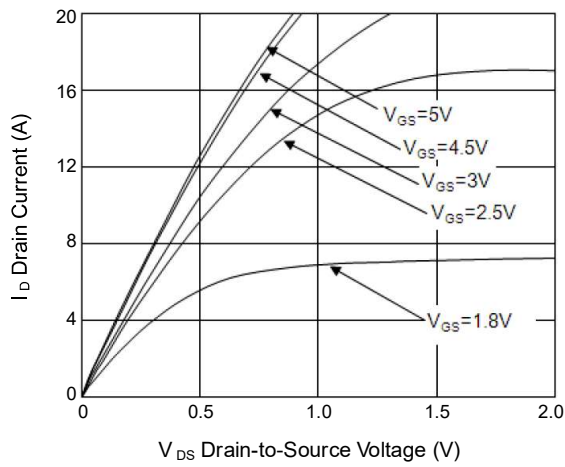


Fig.1 Typical Output Characteristics

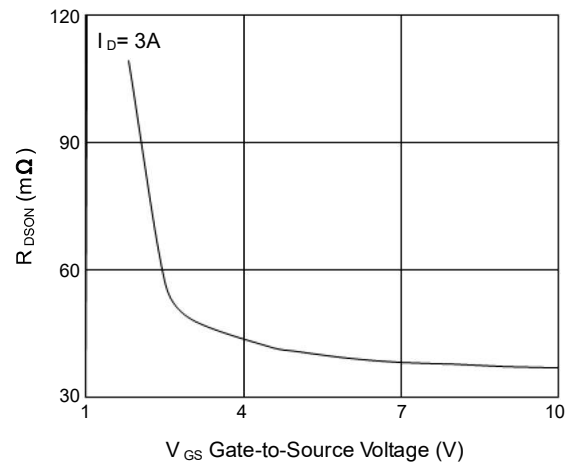


Fig.2 On-Resistance vs. G-S Voltage

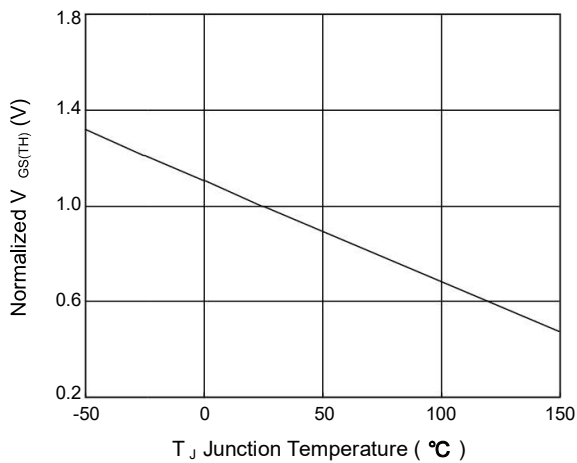


Fig.3 Normalized $V_{GS(th)}$ vs. T_J

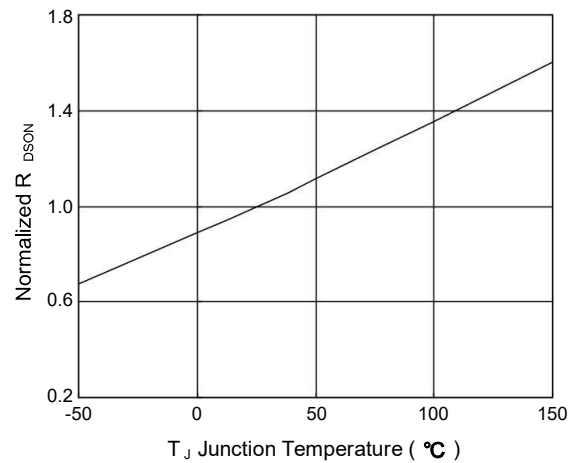


Fig.4 Normalized $R_{DS(on)}$ vs. T_J

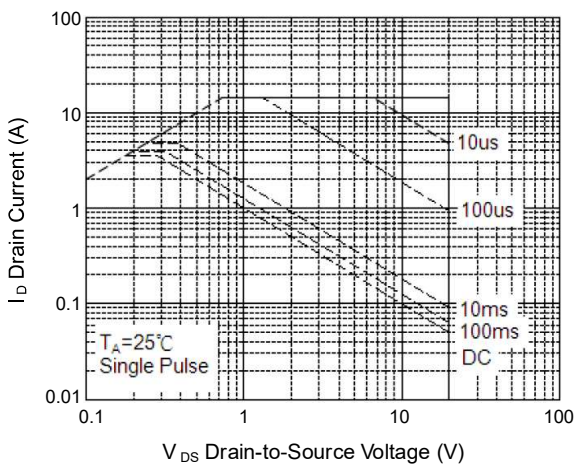


Fig.5 Safe Operating Area

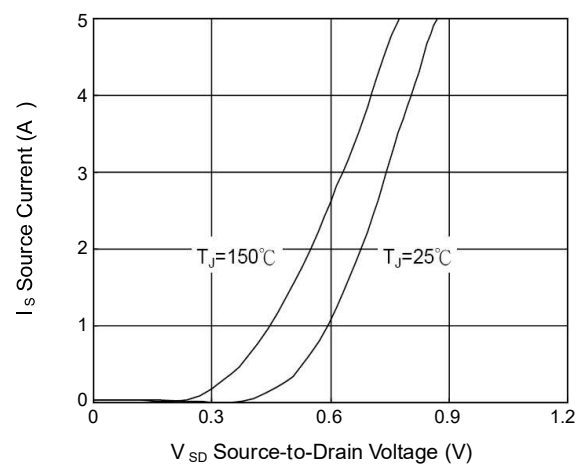
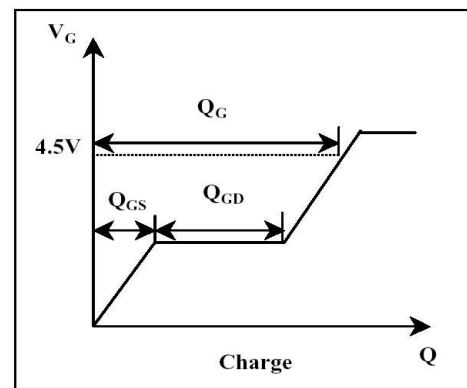
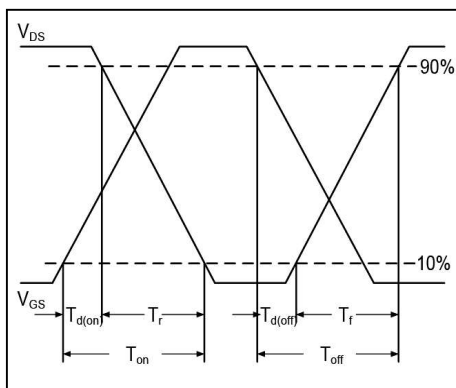
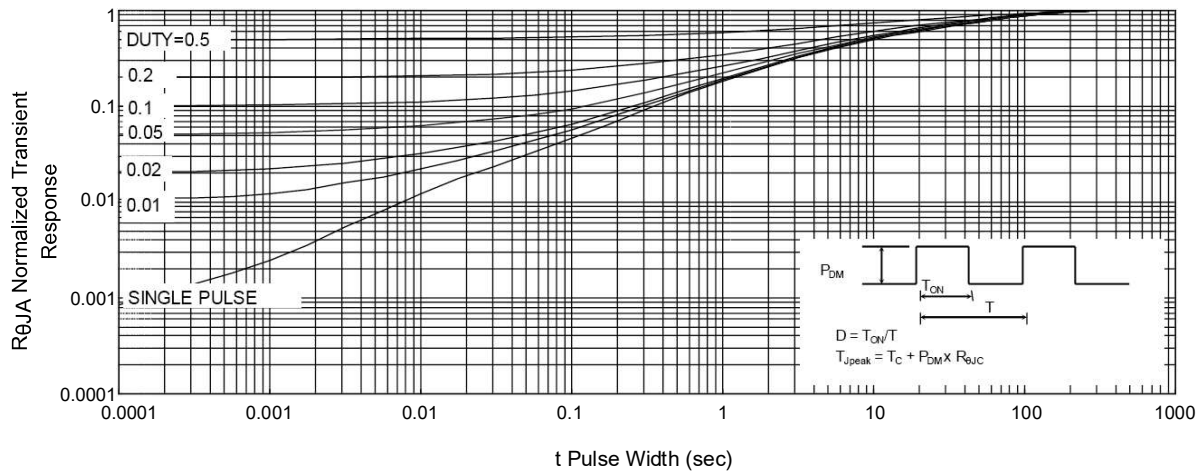
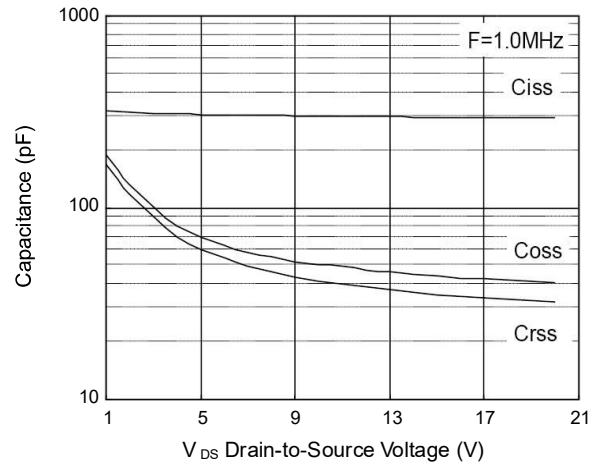
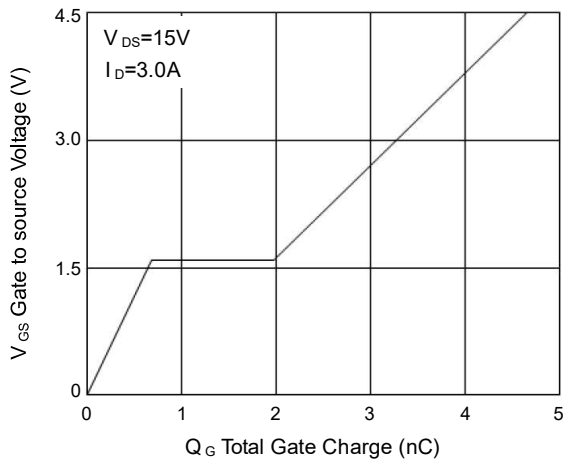
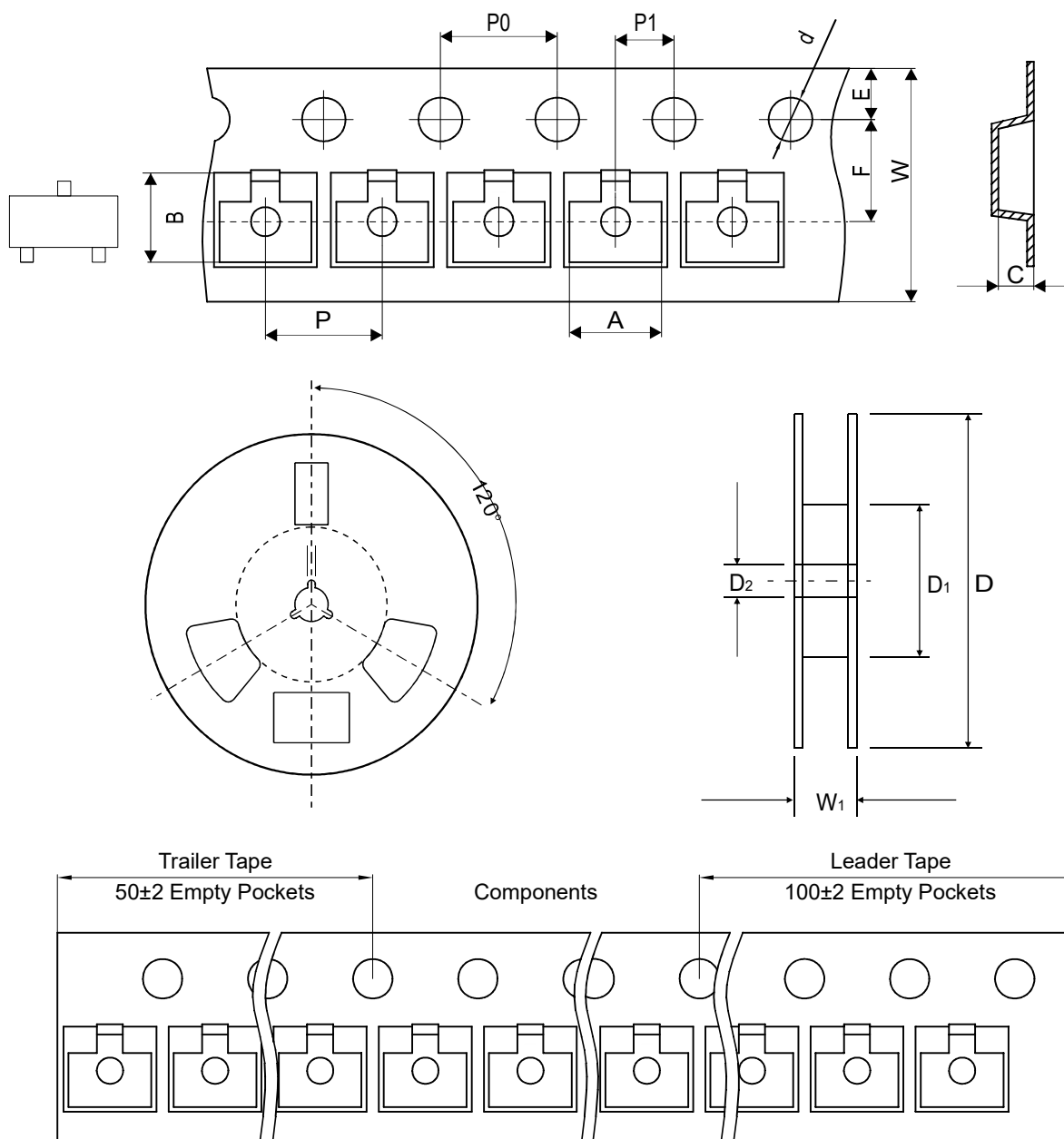


Fig.6 Forward Characteristics of Reverse



Reel Taping Specification



	SYMBOL	A	B	C	d	D	D ₁	D ₂
SOT-23	(mm)	See Note 1			1.50 ± 0.10 - 0.00	330.00 Max.	50.00 Min.	13.00 ± 0.50
	(inch)				0.059 ± 0.004 - 0.000	12.992 Max.	1.969 Min.	0.512 ± 0.020

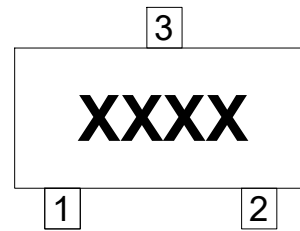
	SYMBOL	E	F	P	P ₀	P ₁	W	W ₁
SOT-23	(mm)	1.75 ± 0.10	3.50 ± 0.05	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	8.30 Max.	14.40 Max.
	(inch)	0.069 ± 0.004	0.138 ± 0.002	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.327 Max.	0.567 Max.

Note: 1. A, B, and C are determined by component size. The clearance between the components and the cavity must be within 0.05mm min. to 0.50mm max.

Company reserves the right to improve product design , functions and reliability without notice.

Marking Code

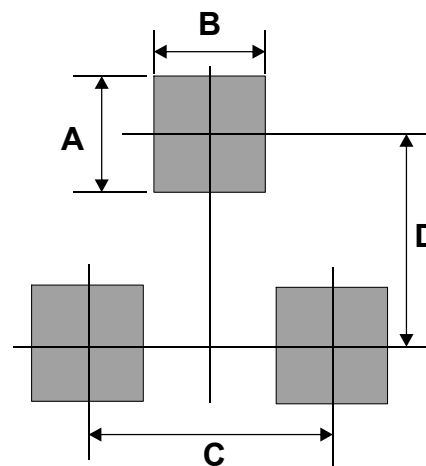
Part Number	Marking Code
CMS2302-HF	2302



XXXX = Product type marking code

Suggested PAD Layout

SIZE	SOT-23	
	(mm)	(inch)
A	0.80	0.035
B	0.60	0.031
C	1.90	0.075
D	2.02	0.080



Standard Packaging

Case Type	Qty Per Reel	Reel Size
	(Pcs)	(inch)
SOT-23	3,000	7